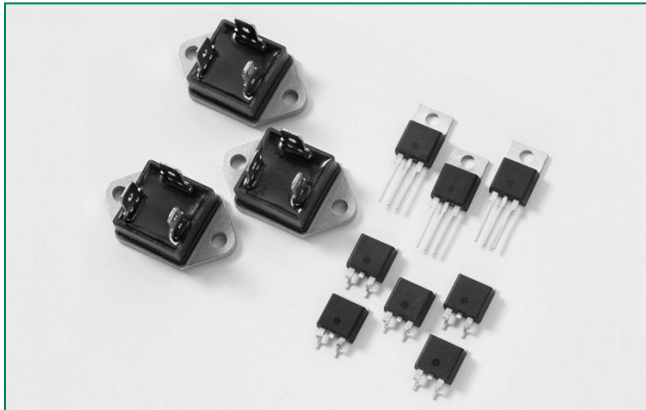


RoHS

## Qxx30xHx & Qxx35xx & Qxx35xHx Series



### Description

30 Amp / 35 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

### Features & Benefits

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 800V
- Surge capability up to 350A
- Electrically isolated package “FASTPAK” & “L - Package” are UL recognized for 2500Vrms

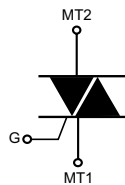
### Agency Approval

Agency	Agency File Number
	FASTPAK & L Package: E71639

### Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	30 & 35	A
$V_{DRM}/V_{RRM}$	400 to 800	V
$I_{GT(Q1)}$	50	mA

### Schematic Symbol



### Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

### Absolute Maximum Ratings – Standard Triac

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx35P5 $T_C = 55^\circ\text{C}$	35 A
$I_{TSM}$	Non repetitive surge peak on-state current (full cycle, $T_J$ initial = $25^\circ\text{C}$ )	f = 50 Hz t = 20 ms	300
		f = 60 Hz t = 16.7 ms	350
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3$ ms	508 $\text{A}^2\text{s}$
di/dt	Critical rate of rise of on-state current ( $I_G = 200\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time)	f = 120 Hz $T_J = 125^\circ\text{C}$	100 $\text{A}/\mu\text{s}$
$I_{GTM}$	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$ $I_{GT} \leq I_{GTM}$ $T_J = 125^\circ\text{C}$	2 A
$P_{G(AV)}$	Average gate power dissipation	$T_J = 125^\circ\text{C}$	0.5 W
$T_{stg}$	Storage temperature range		-40 to 125 $^\circ\text{C}$
$T_J$	Operating junction temperature range		-25 to 125 $^\circ\text{C}$

Note: xx = voltage

**Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)**

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx35RH5/Qxx35NH5	$T_C = 90^\circ\text{C}$	35	A
		Qxx30LH5	$T_C = 50^\circ\text{C}$	30	
$I_{TSM}$	Non repetitive surge peak on-state current (full cycle, $T_J$ initial = $25^\circ\text{C}$ )	f = 50 Hz	t = 20 ms	290	A
		f = 60 Hz	t = 16.7 ms	350	
$I^2t$	$I^2t$ Value for fusing		$t_p = 8.3$ ms	508	$\text{A}^2\text{s}$
di/dt	Critical rate of rise of on-state current ( $I_G = 200\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time)	f = 120 Hz	$T_J = 125^\circ\text{C}$	100	$\text{A}/\mu\text{s}$
$I_{GTM}$	Peak gate trigger current	$t_p \leq 10 \mu\text{s}$ $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	2	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.5	W
$T_{stg}$	Storage temperature range			-40 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range			-25 to 125	$^\circ\text{C}$

**Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified) — Standard Triac**

Symbol	Test Conditions	Quadrant		Qxx35P5	Unit
$I_{GT}$	$V_D = 12\text{V}$ $R_L = 30 \Omega$	I – II – III	MAX.	50	mA
		IV	TYP.	120	
$V_{GT}$		I – II – III	MAX.	2.75	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{k}\Omega$ $T_J = 110^\circ\text{C}$	ALL	MIN.	0.2	V
$I_H$	$I_T = 400\text{mA}$		MAX.	50	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	600V	MIN.	475	$\text{V}/\mu\text{s}$
		800V		400	
(dv/dt)c	(di/dt)c = 18.9 A/ms $T_J = 125^\circ\text{C}$		TYP.	5	$\text{V}/\mu\text{s}$
$t_{gt}$	$I_G = 2 \times I_{GT}$ PW = 15 $\mu\text{s}$ $I_T = 49.5\text{A(pk)}$		TYP.	3	$\mu\text{s}$

**Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified) — Alternistor Triac (3 Quadrants)**

Symbol	Test Conditions	Quadrant		Qxx35RH5 Qxx35NH5 Qxx30LH5	Unit
$I_{GT}$	$V_D = 12\text{V}$ $R_L = 30 \Omega$	I – II – III	MAX.	50	mA
		I – II – III	MAX.	2	
$V_{GT}$		I – II – III	MAX.	2	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{k}\Omega$ $T_J = 125^\circ\text{C}$	I – II – III	MIN.	0.2	V
$I_H$	$I_T = 400\text{mA}$		MAX.	75	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	475	$\text{V}/\mu\text{s}$
		600V		400	
(dv/dt)c	(di/dt)c = 18.9 A/ms $T_J = 125^\circ\text{C}$		MIN.	20	$\text{V}/\mu\text{s}$
$t_{gt}$	<b>35A device</b> $I_G = 2 \times I_{GT}$ PW = 15 $\mu\text{s}$ $I_T = 49.5\text{A(pk)}$		TYP.	3	$\mu\text{s}$
	<b>30A device</b> $I_G = 2 \times I_{GT}$ PW = 15 $\mu\text{s}$ $I_T = 42.4\text{A(pk)}$				

Note: xx = voltage

**Static Characteristics**

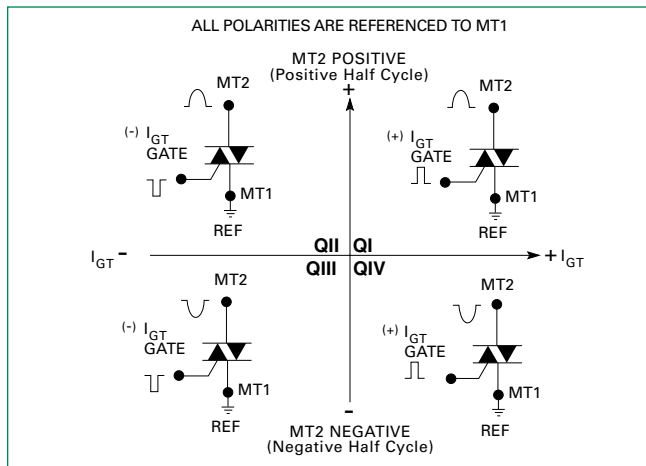
Symbol	Test Conditions			Value	Unit		
$V_{TM}$	35A device $I_{TM} = 49.5A$ $t_p = 380 \mu s$			MAX.	1.5	V	
	30A device $I_{TM} = 42.4A$ $t_p = 380 \mu s$				1.4		
$I_{DRM}$ $I_{RRM}$	$V_D = V_{DRM} / V_{RRM}$	Qxx35P5	$T_J = 25^\circ C$	600 - 800V	MAX.	100	$\mu A$
			$T_J = 125^\circ C$	600 - 800V		5	mA
		Qxx35R/NH5 Qxx30LH5	$T_J = 25^\circ C$	400 - 600V	MAX.	10	$\mu A$
			$T_J = 125^\circ C$	400 - 600V		2	mA

**Thermal Resistances**

Symbol	Parameter	Value	Unit	
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx35P5	1.50	$^\circ C/W$
		Qxx35RH5 / Qxx35NH5	0.85	
		Qxx30LH5	2.30	
$R_{\theta(J-A)}$	Junction to ambient	Qxx35RH5	45	$^\circ C/W$
		Qxx30LH5	50	

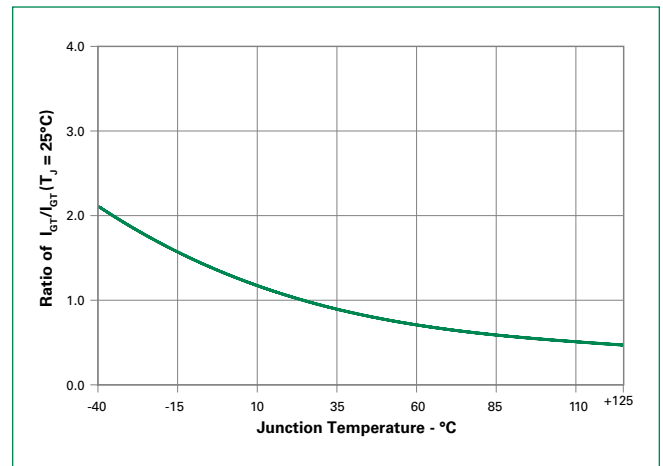
Note: xx = voltage

**Figure 1: Definition of Quadrants**

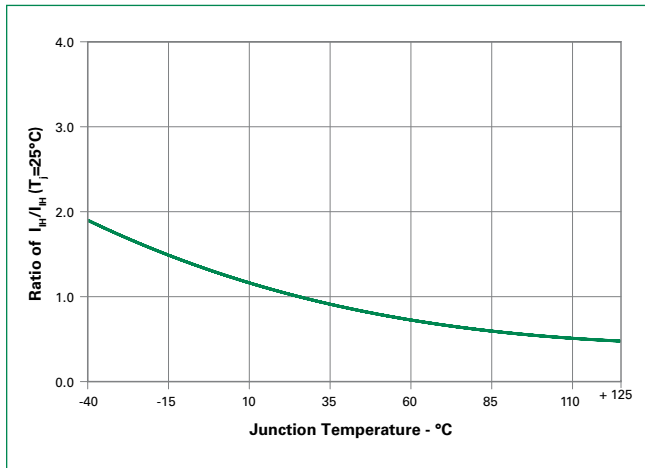


Note: Alternistors will not operate in QIV

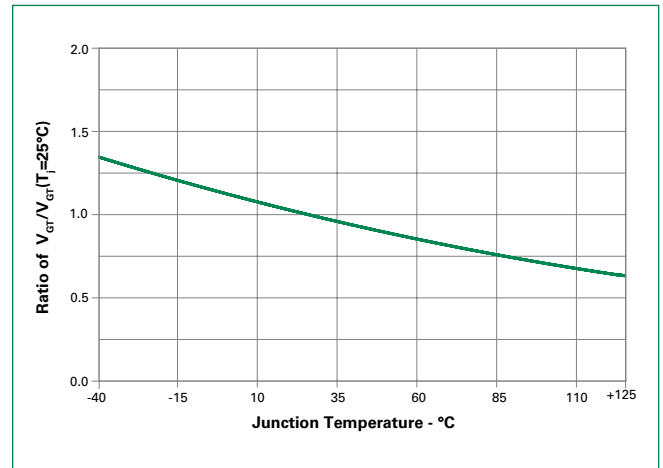
**Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature**



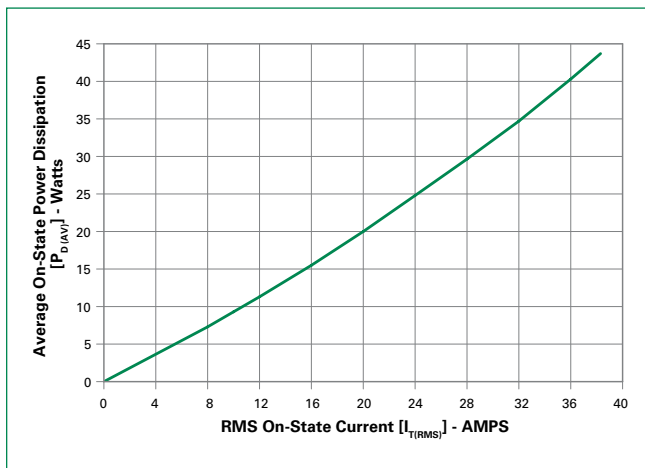
**Figure 3: Normalized DC Holding Current vs. Junction Temperature**



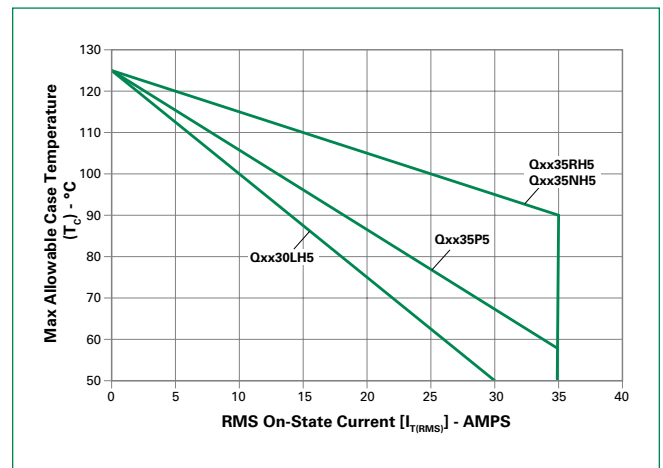
**Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature**



**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



**Figure 6: Maximum Allowable Case Temperature vs. On-State Current**



Note: xx = voltage

**Figure 7: On-State Current vs. On-State Voltage (Typical)**

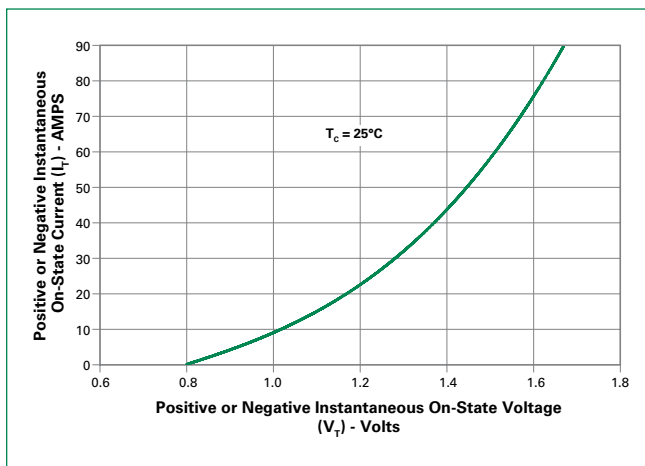
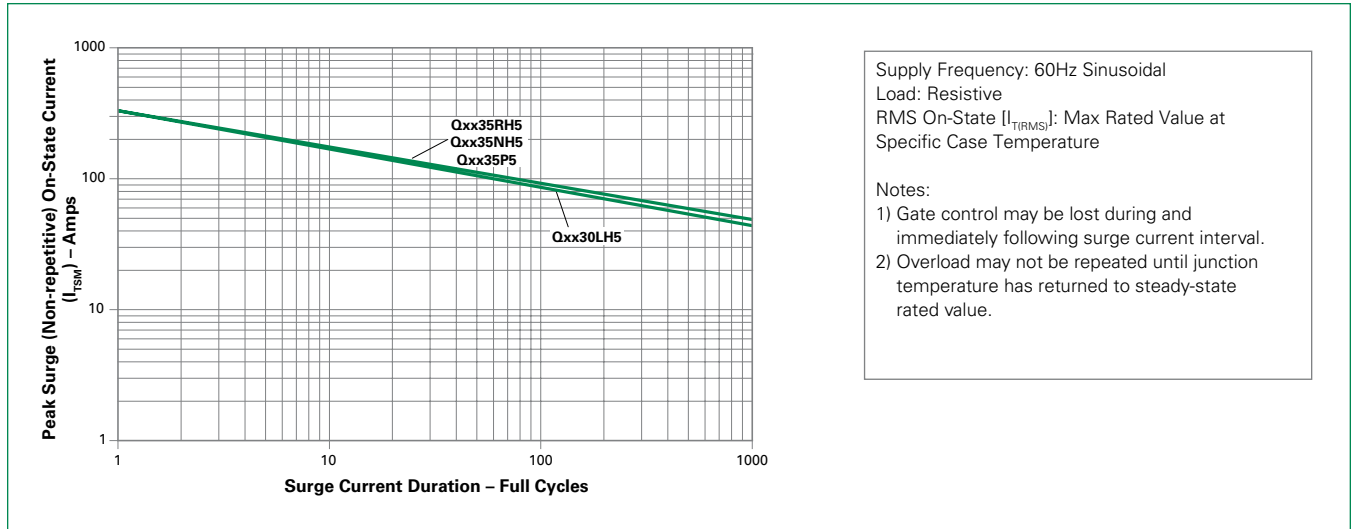


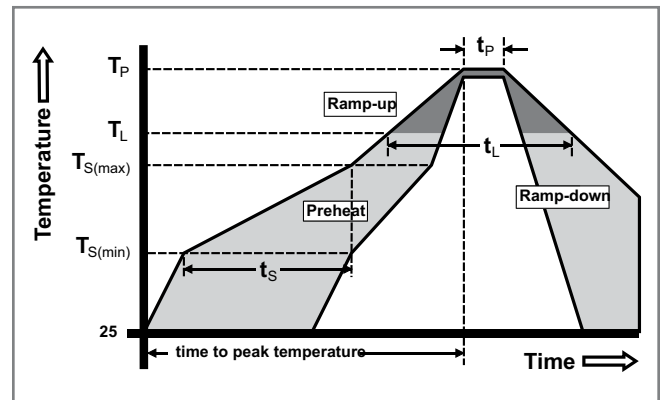
Figure 8: Surge Peak On-State Current vs. Number of Cycles



Note: xx = voltage

Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Time (min to max) ( $t_s$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



### Physical Specifications

<b>Terminal Finish</b>	100% Matte Tin-plated.
<b>Body Material</b>	UL recognized epoxy meeting flammability classification 94V-0.
<b>Terminal Material</b>	Copper Alloy

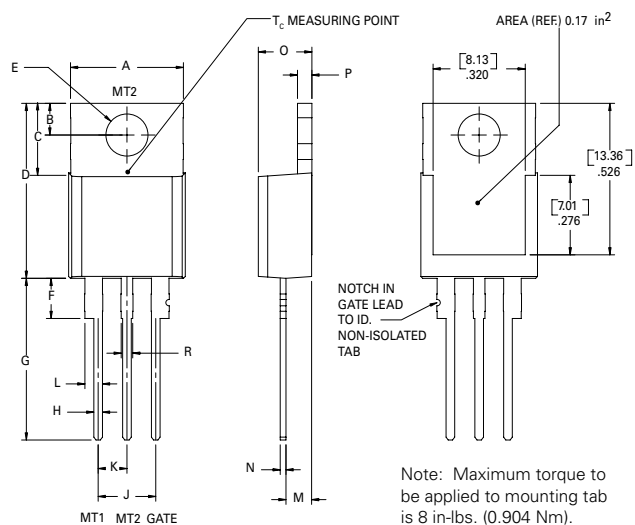
### Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### Environmental Specifications

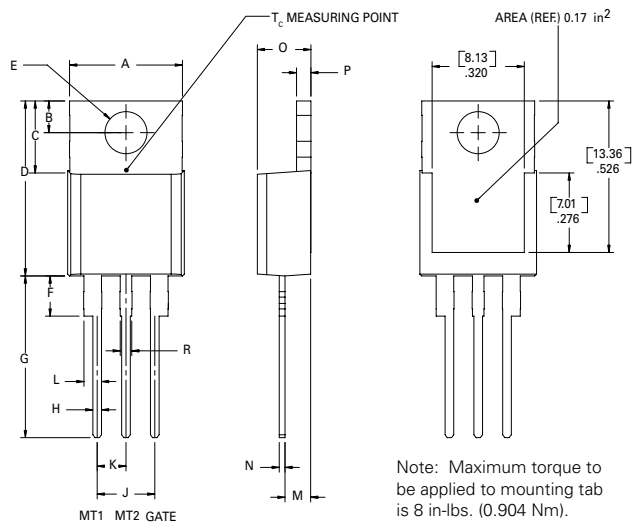
Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Thermal Shock</b>	MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature
<b>Autoclave</b>	EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E

### Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



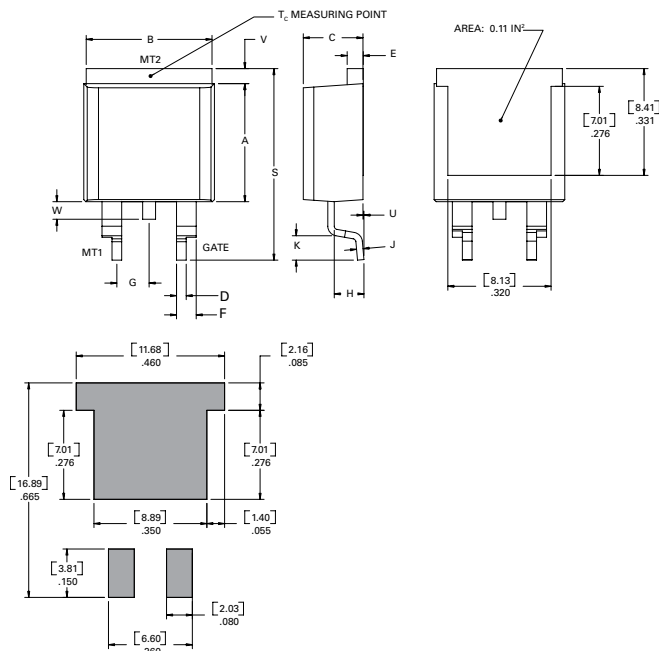
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

### Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



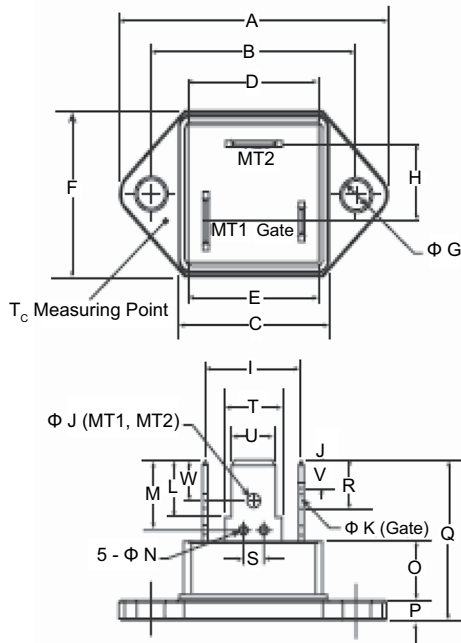
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

### Dimensions — TO-263 (N-Package) — D<sup>2</sup> Pak Surface Mount



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
E	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.016	1.78

**Dimensions — TO-3 Fastpak (P Package) — Isolated Mounting Tab**



Thickness of all three copper-alloy terminals is .032" (0.81mm)

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	1.531	1.543	38.90	39.20
B	1.177	1.185	29.90	30.10
C	0.843	0.850	21.40	21.60
D	0.780	0.795	19.80	20.20
E	0.783	0.791	19.90	20.10
F	0.874	0.906	22.20	23.00
G	0.161	0.169	4.10	4.30
H	0.386	0.465	9.80	11.80
I	0.508	0.587	12.90	14.90
J	0.079	0.087	2.00	2.20
K	0.047	0.055	1.20	1.40
L	0.307	0.319	7.80	8.10
M	0.372	0.396	9.45	10.05
N	0.043	0.059	1.10	1.50
O	0.315	0.331	8.00	8.40
P	0.098	0.106	2.50	2.70
Q	0.846	0.886	21.50	22.50
R	0.244	0.256	6.20	6.50
S	0.106	0.130	2.70	3.30
T(MT1)	0.321	0.329	8.15	8.35
T(MT2)	0.321	0.329	8.15	8.35
T(Gate)	0.220	0.228	5.60	5.80
U(MT1)	0.246	0.254	6.25	6.45
U(MT2)	0.246	0.254	6.25	6.45
U(Gate)	0.183	0.191	4.65	4.85
V	0.120	0.130	3.05	3.30
W	0.175	0.185	4.45	4.70

Maximum torque to be applied to mounting tab is 8 in-lbs (0.904 Nm)

**Product Selector**

Part Number	Voltage			Gate Sensitivity Quadrants		I <sub>T(RMS)</sub>	Type	Package
	400V	600V	800V	I – II – III	IV			
Qxx35P5		X	X	50 mA	120 mA (TYP)	35A	Standard Triac	FASTPACK
Qxx35RH5	X	X		50 mA		35A	Alternistor Triac	TO-220R
Qxx35NH5	X	X		50 mA		35A	Alternistor Triac	TO-263 D <sup>2</sup> -PAK
Qxx30LH5	X	X		50 mA		30A	Alternistor Triac	TO-220L

Note: xx = Voltage



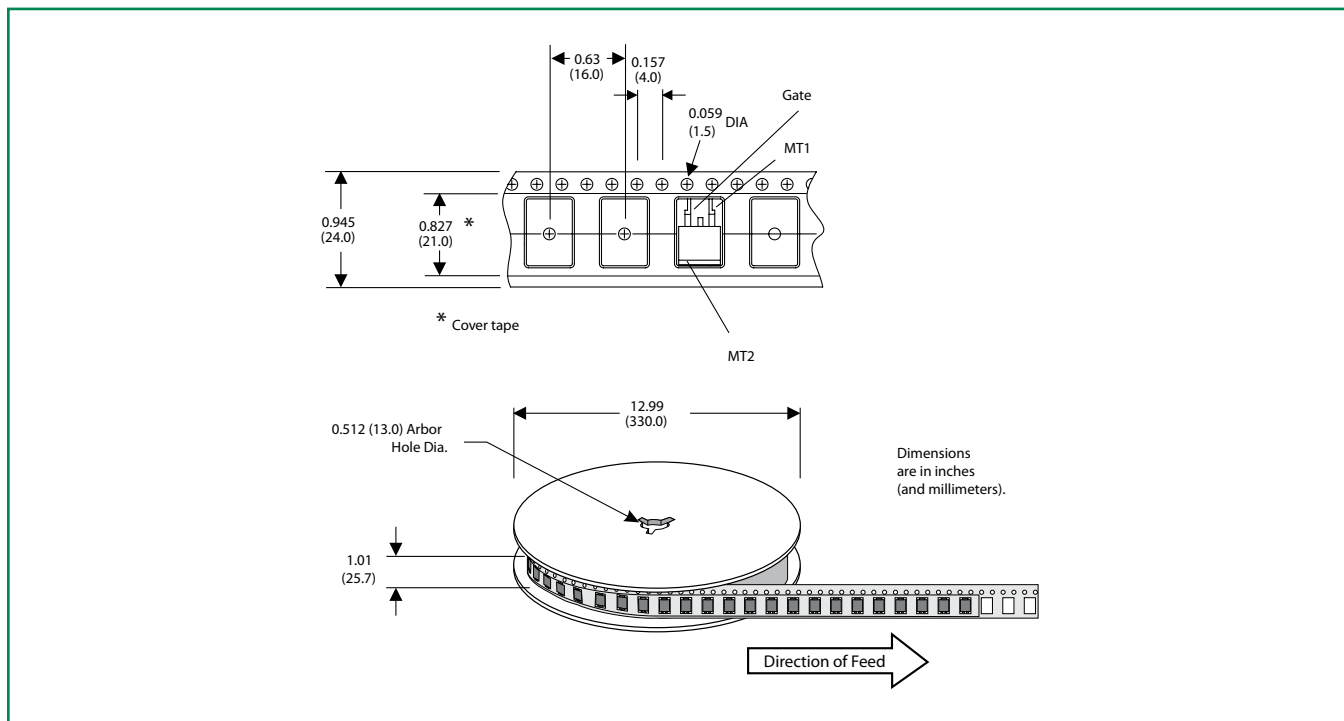
### Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx30LH5	Qxx30LH5	2.20 g	Bulk	500
Qxx30LH5TP	Qxx30LH5	2.20 g	Tube	500 (50 per tube)
Qxx35RH5	Qxx35RH5	2.20 g	Bulk	500
Qxx35RH5TP	Qxx35RH5	2.20 g	Tube	500 (50 per tube)
Qxx35NH5TP	Qxx35NH5	1.60 g	Tube	500 (50 per tube)
Qxx35NH5RP	Qxx35NH5	1.60 g	Embossed Carrier	500
Qxx35P5	Qxx35P5	21.4 g	Bulk	200

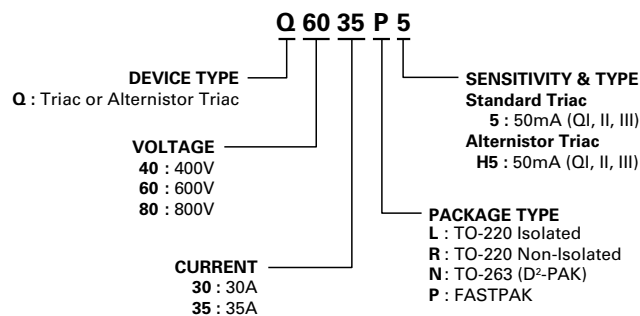
Note: xx = Voltage

### TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



### Part Numbering System



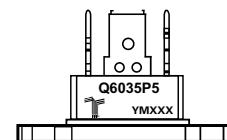
### Part Marking System

TO-220 AB – (R Package)  
TO-263 AB – (N Package)



TO-220 AB – (L Package)

FASTPAK (P Package)



## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9